# VS-HFA70EA120

### **Vishay Semiconductors**



HEXFRED<sup>®</sup> Ultrafast Soft Recovery Diode, 70 A



PRIMARY CHARACTERISTICS						
V <sub>R</sub>	1200 V					
V <sub>F</sub> (typical)	2.2 V					
t <sub>rr</sub> (typical)	48 ns					
$I_{F(DC)}$ at $T_C$ , per module	70 A at 121 °C					
Package	SOT-227					

### FEATURES

- Fast recovery time characteristic
- Electrically isolated base plate
- Antiparallel diodes
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- · Designed and qualified for industrial level
- UL approved file E78996
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **DESCRIPTION / APPLICATIONS**

This SOT-227 modules with HEXFRED<sup>®</sup> rectifier are in antiparallel configuration. The antiparallel configuration is used for simple series rectifier and high voltage application. The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are intended for general applications such as HV power supplies, electronic welders, motor control and inverters.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Cathode to anode voltage	V <sub>R</sub>		1200	V		
Continuous forward current, per leg	١ <sub>F</sub>	T <sub>C</sub> = 121 °C	35	٨		
Single pulse forward current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	350	A		
Martin and a state to the state of the	Р	T <sub>C</sub> = 25 °C	357	W		
Maximum power dissipation, per leg	PD	T <sub>C</sub> = 100 °C	143	vv		
RMS isolation voltage	VISOL	Any terminal to case, t = 1 minute	2500	V		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA	1200	-	-			
		I <sub>F</sub> = 30 A	-	2.2	3.0			
Forward voltage, per leg	V <sub>FM</sub>	I <sub>F</sub> = 60 A	-	2.8	4.0	V		
		I <sub>F</sub> = 30 A, T <sub>J</sub> = 125 °C	-	2.13	-			
		I <sub>F</sub> = 60 A, T <sub>J</sub> = 125 °C	-	2.70	-			
		I <sub>F</sub> = 30 A, T <sub>J</sub> = 150 °C	-	2.04	-			
		I <sub>F</sub> = 60 A, T <sub>J</sub> = 150 °C	-	2.65	-			
Reverse leakage current, per leg		$V_{R} = V_{R}$ rated	-	2.0	75	μA		
	I <sub>RM</sub>	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	1.6	5	<b>m</b> (		
		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	5	10	mA		



COMPLIANT

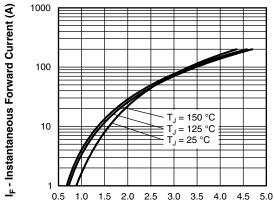


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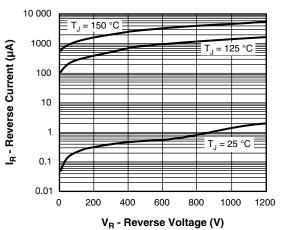
<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 \text{ A}; \text{ d}I_F/\text{d}$	It = 200 A/ $\mu$ s; V <sub>R</sub> = 30 V	-	48	-		
Reverse recovery time, per leg	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 50 A dI <sub>F</sub> /dt = - 200 A/μs V <sub>B</sub> = 200 V	-	145	-	ns	
		T <sub>J</sub> = 125 °C		-	218	-		
Peak recovery current, per leg	1	T <sub>J</sub> = 25 °C		-	13	-	А	
Feak recovery current, per leg	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	19	-	~	
Poverse receivers charge per leg	0	T <sub>J</sub> = 25 °C	v <sub>R</sub> – 200 v	-	910	-	nC	
Reverse recovery charge, per leg	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	1920	-	nc	
Junction capacitance, per leg	CT	V <sub>R</sub> = 1200 V		-	27	_	pF	

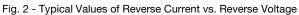
THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Junction to case, single leg conducting	Б		-	-	0.35		
Junction to case, both legs conducting	R <sub>thJC</sub>		-	-	0.175	°C/W	
Case to heatsink	R <sub>thCS</sub>	Flat, greased surface	-	0.05	-		
Weight			-	30	-	g	
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)	
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)	
Case style				S	OT-227		

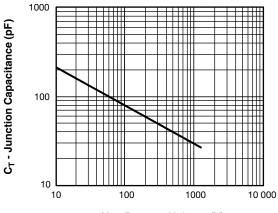


V<sub>FM</sub> - Forward Voltage Drop (V)

Fig. 1 - Typical Forward Voltage Drop Characteristics







**V<sub>R</sub> - Reverse Voltage (V)** Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

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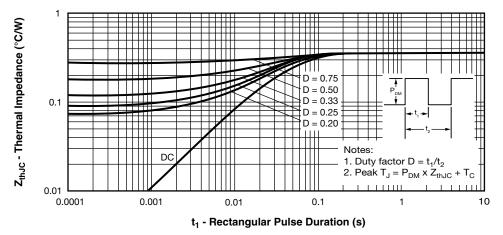
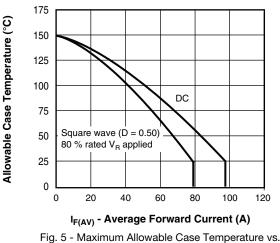


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics



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Average Forward Current

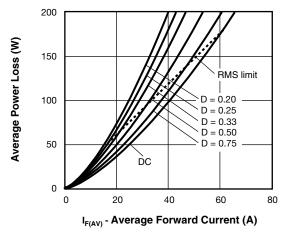
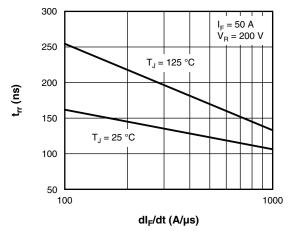


Fig. 6 - Forward Power Loss Characteristics



<sup>1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} \mbox{Pd} = \mbox{Forward power loss} = \mbox{I}_{F(AV)} \times \mbox{V}_{FM} \mbox{ at } (\mbox{I}_{F(AV)}/\mbox{D}) \mbox{ (see fig. 5);} \\ \mbox{Pd}_{REV} = \mbox{Inverse power loss} = \mbox{V}_{R1} \times \mbox{I}_{R} \mbox{ (1 - D); } \mbox{I}_{R} \mbox{ at } \mbox{V}_{R1} = \mbox{Rated V}_{R} \end{array}$ 





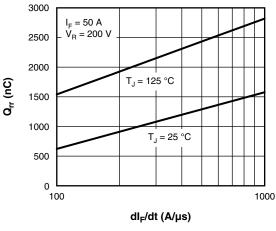


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

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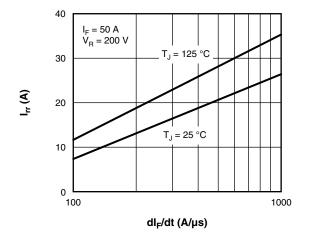


Fig. 9 - Typical Peak Recovery Current vs. dl<sub>F</sub>/dt

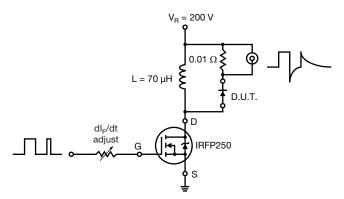
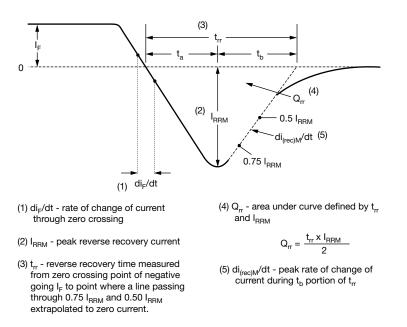
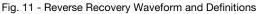


Fig. 10 - Reverse Recovery Parameter Test Circuit



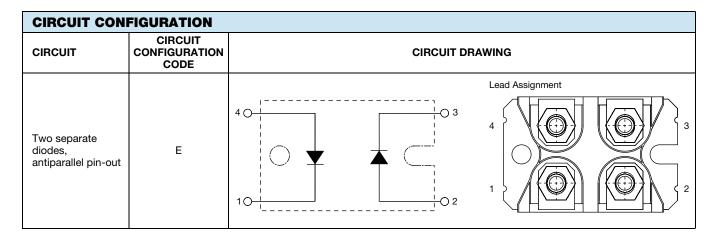






#### **ORDERING INFORMATION TABLE**

Device code	VS-	HF	Α	70	Е	Α	120	
		2	3	4	5	6	7	
	님	- Vishay Semiconductors product						
	2 -	HE	HEXFRED <sup>®</sup> family					
	3 -	Pro	Process designator (A = electron irradiated)					
	4 -	Ave	Average current (70 = 70 A)					
	5 -	Circ	Circuit configuration (two separate diodes, antiparallel pin-out)					
	6 -	Pac	Package indicator (SOT-227 standard insulated base)					
	7 -	Vol	Voltage rating (120 = 1200 V)					



LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95423						
Part marking information	www.vishay.com/doc?95425					

**Vishay Semiconductors** 



SOT-227 Generation 2

#### **DIMENSIONS** in millimeters (inches)



#### Note

• Controlling dimension: millimeter



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